



PADRE CONCEIÇÃO COLLEGE OF ENGINEERING

Verna - Goa

Department of Basic Science and Humanities

Roll No:

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Re-Internal Test-I

Semester & Course: I (RC 2019-20)

Subject: FE 120 Physics

Course Instructor: Swapna Narvekar

Date: 8/2/2022

Time: 10am-12pm

Max Marks: 25

Instructions: Attempt all questions. Assume missing data, if any and justify.

	<u>Marks</u>	<u>CO</u>	<u>CL</u>
Q1. Explain interference in a parallel thin film for reflected light and derive the conditions for maxima and minima; with a neat ray diagram.	[5]	FE120.1	CL2
Q2. Find Diffusion coefficients of electrons and holes of a semiconductor at 28 °C , if mobilities of electrons and holes are 0.19 and 0.027 m²/Vs respectively.	[5]	FE120.2	CL3
Q3. Derive an expression for conductivity of a semiconductor in terms of a mobility of charge carriers.	[5]	FE120.2	CL2
Q4. The area of a hysteresis loop drawn between B and H is 220m² . Each unit space along the vertical axis represent 0.02 Wb/m² and each unit space along the horizontal axis represents 30A/m . Determine the hysteresis loss per cycle.	[4]	FE120.2	CL3
Q5. Distinguish between soft magnetic materials and hard magnetic materials. Draw diagrams of B-H curve for each.	[6]	FE120.2	CL2
